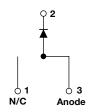


HEXFRED® Ultrafast Soft Recovery Diode, 16 A



TO-263AB (D²PAK)



PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
I _{F(AV)}	16 A						
V_{R}	1200 V						
V _F at I _F	2.3 V						
t _{rr} (typ.)	30 ns						
T _J max.	150 °C						
Diode variation	Single die						

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





RoHS COMPLIANT

HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TB120SPbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120SPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120SPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Cathode to anode voltage	V_{R}		1200	V				
Maximum continuous forward current	I _F	T _C = 100 °C	16					
Single pulse forward current	I _{FSM}		190	Α				
Maximum repetitive forward current	I _{FRM}		64					
Maximum nawar dissination	D-	T _C = 25 °C	151	W				
Maximum power dissipation	P_D	T _C = 100 °C	60	VV				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				





ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage	V _{FM}	I _F = 16 A		-	2.5	3.0	V		
		I _F = 32 A	See fig. 1	-	3.2	3.93			
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7			
Maximum reverse			See fig. 2	1	0.75	20			
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	375	2000	μA		
Junction capacitance	C _T	$V_R = 200 \text{ V}$ See fig. 3		-	27	40	pF		
Series inductance	L _S	Measured lead to lead 5 mm from page 1	ackage body	-	8.0	-	nΗ		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V _R = 30 V	-	30	-	ns		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135			
	t _{rr2}	T _J = 125 °C		=	164	245			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C	$I_F = 16 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	=	5.8	10	A nC		
	I _{RRM2}	T _J = 125 °C		-	8.3	15			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675			
See fig. 7	Q _{rr2}	T _J = 125 °C		=	680	1838	iiC		
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	- A/μs		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	NVV			
Weight			-	2.0	-	g			
vveigni			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D ² PAK)		HFA16	TB120S				



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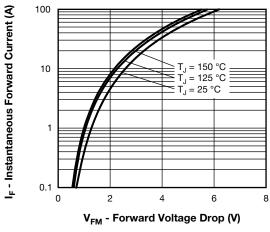


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

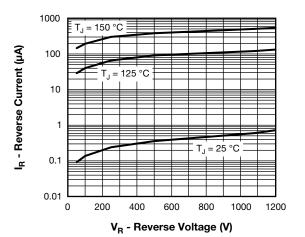


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

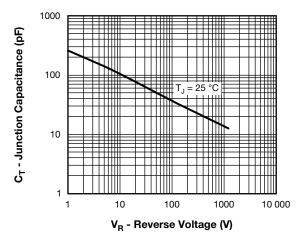


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

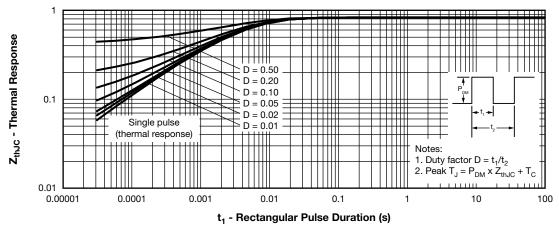


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)





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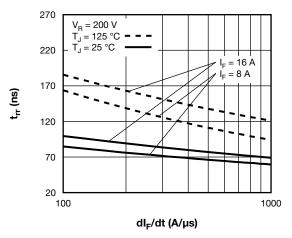


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

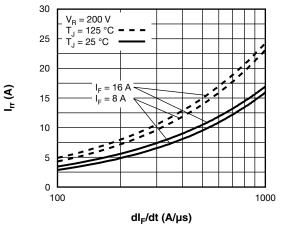


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

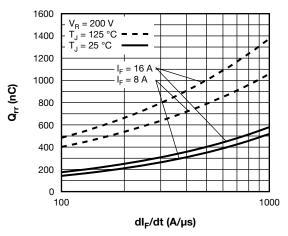


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

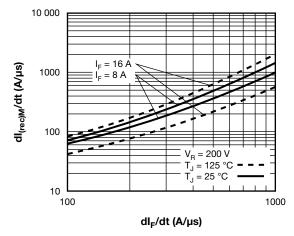


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

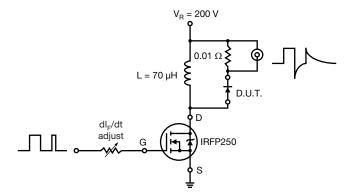
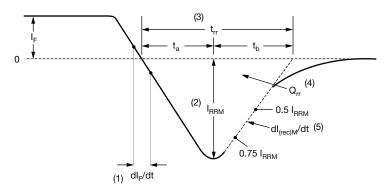


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

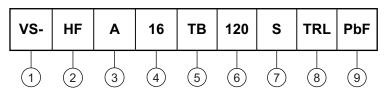
(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Process designator: A = electron irradiated

4 - Current rating (16 = 16 A)

5 - Package outline (TB = TO-220, 2 leads)

6 - Voltage rating (120 = 1200 V)

8 - • None = tube

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - • PbF = lead (Pb)-free

• P = lead (Pb)-free (for D²PAK TRR and TRL)

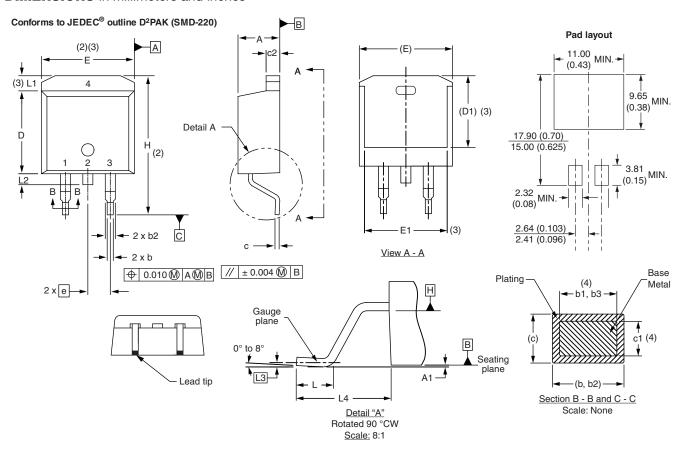
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TB120SPBF	50	1000	Antistatic plastic tube						
VS-HFA16TB120STRRP	800	800	13" diameter reel						
VS-HFA16TB120STRLP	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	2.54 BSC 0.100 BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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